

IGBT MODULE (F series)

■ Features

- Low Saturation Voltage
- Voltage Drive
- Variety of Power Capacity Series

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial Machines, such as Welding Machines

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V _{CES}	1200	V
Gate-Emitter Voltage	V _{GES}	±20	V
Collector Current	Continuous	I _c	100
	1ms	I _{c pulse}	200
	Continuous	-I _c	100
	1ms	-I _{c pulse}	200
Max. Power Dissipation	P _c	720	W
Operating Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-40 to +125	°C
Net. Weight		400	g
Isolation Voltage	AC. 1min.	V _{isol}	2500 V
Screw Torque	Mounting *1	3.5 {35}	N · m
	Terminals *1	3.5 {35}	{kg · cm}

*1 Recommendable Value 2.5 to 3.5 N·m {25 to 35 kg·cm} (M5)

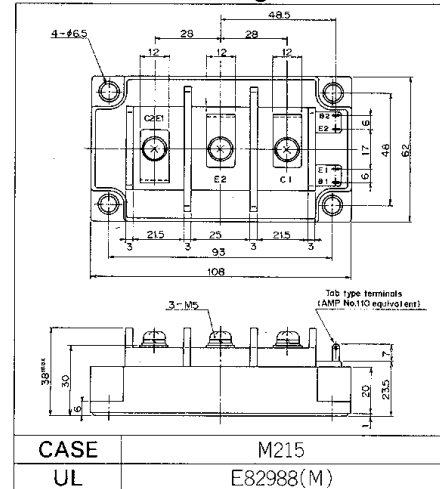
● Electrical Characteristics (T_c=25°C)

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I _{CES}	V _{GE} =0V V _{CE} =1200V T _j =25°C			1.0	mA
		V _{GE} =0V V _{CE} =1200V T _j =125°C				mA
Gate-Emitter Leakage Current	I _{GES}	V _{CE} =0V V _{GE} =±20V			200	nA
Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{CE} =20V I _c =100mA	3.0		6.0	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V I _c =100A			2.5	V
Input Capacitance	C _{ies}	V _{GE} =0V		18000		pF
Output Capacitance	C _{oes}	V _{CE} =10V				
Reverse Transfer Capacitance	C _{res}	f=1MHz				
Turn-on Time	t _{on}	V _{CC} =600V I _c =100A	Resistive load		0.8	μs
	t _r				0.6	
Turn-off Time	t _{off}	V _{GE} =±15V R _G =9.1Ω	Inductive load		1.5	
	t _r				1.0	
Diode Forward On-Voltage	V _F	I _F =100A, V _{GE} =0V			2.5	V
Reverse Recovery Time	t _{rr}	I _F =100A, -di/dt=300A/μs V _{GE} =-10V			350	ns

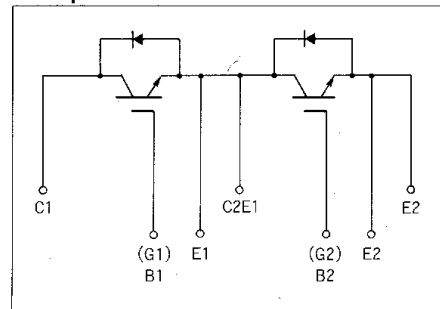
● Thermal Characteristics

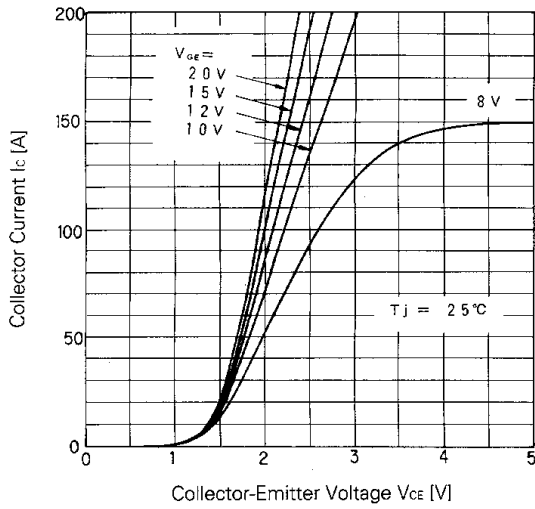
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	R _{th(j-c)}	IGBT			0.174	°C/W
	R _{th(j-e)}	Diode			0.333	
	R _{th(c-f)}	With Thermal compound		0.025		

■ Outline Drawings

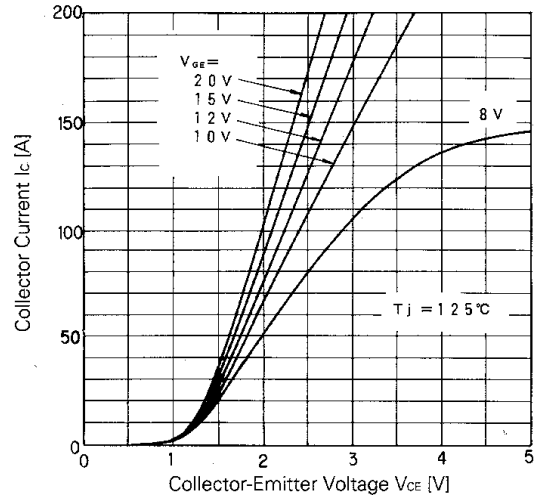


■ Equivalent Circuit Schematic

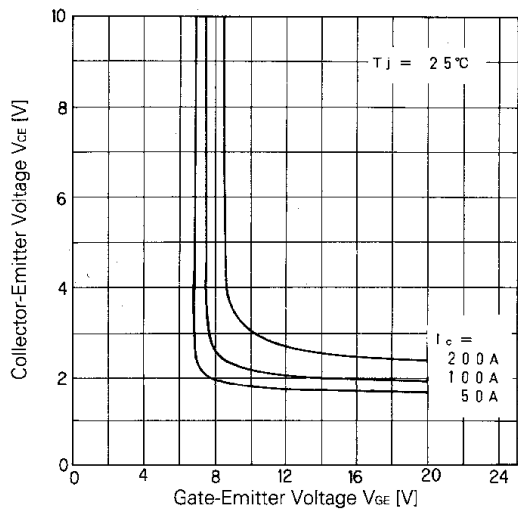




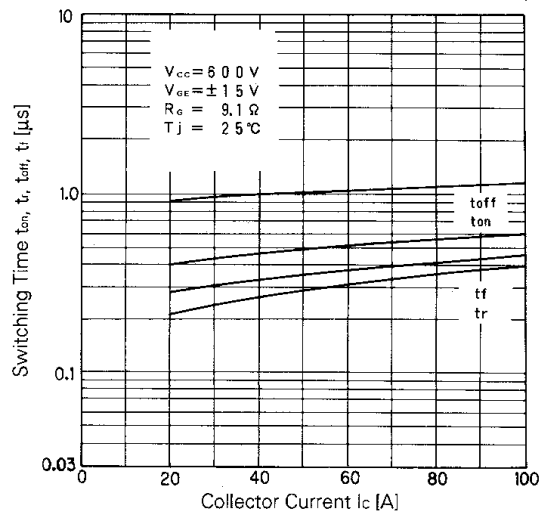
Collector Current vs. Collector-Emitter Voltage



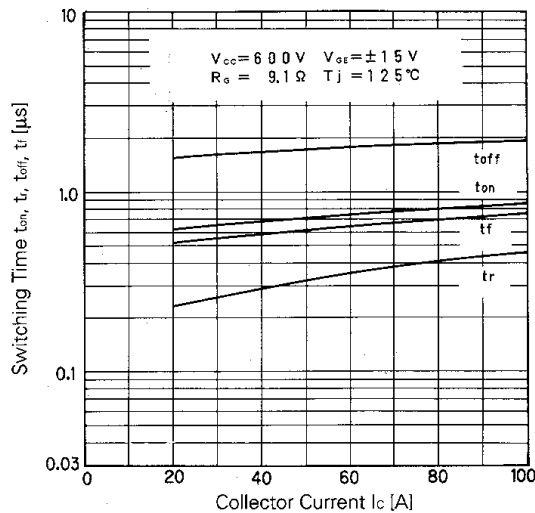
Collector Current vs. Collector-Emitter Voltage



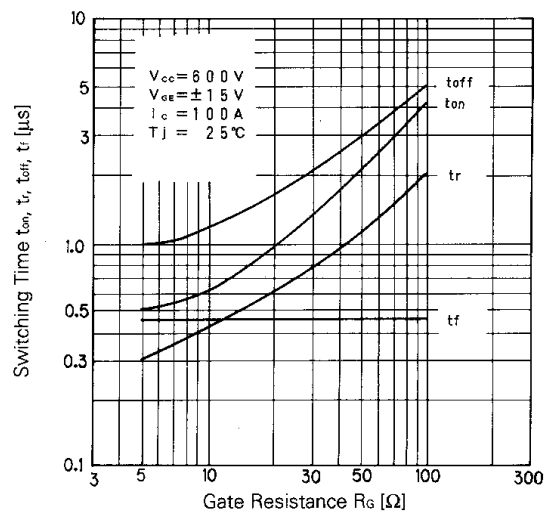
Collector-Emitter Voltage vs. Gate-Emitter Voltage



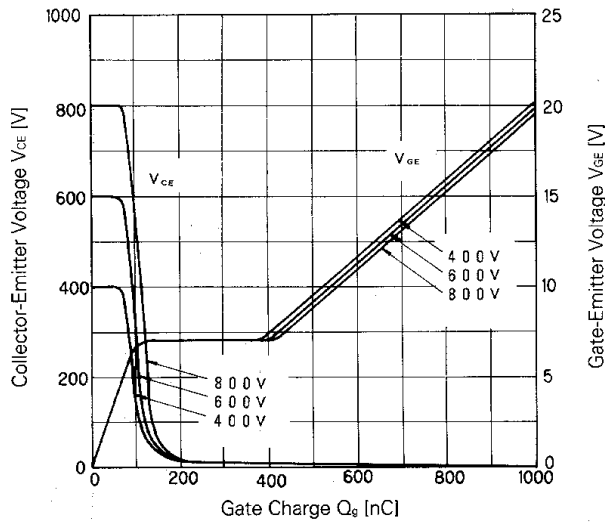
Switching Time



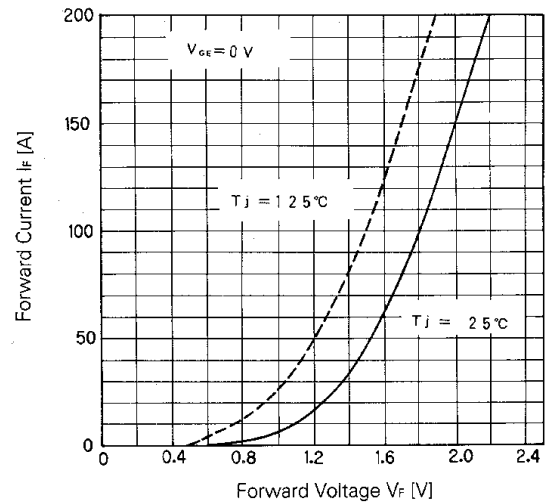
Switching Time



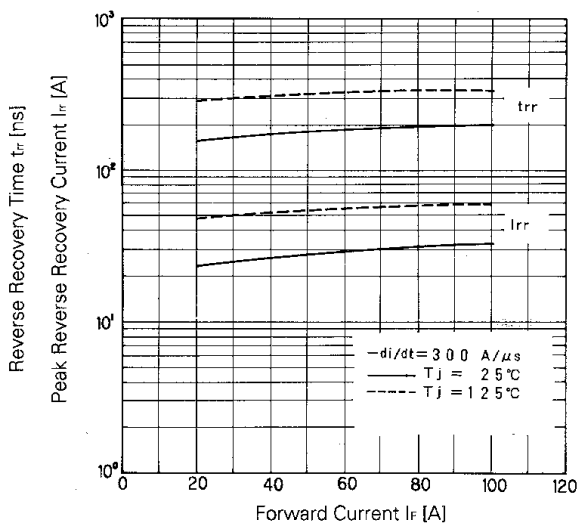
Switching Time-Gate Resistance



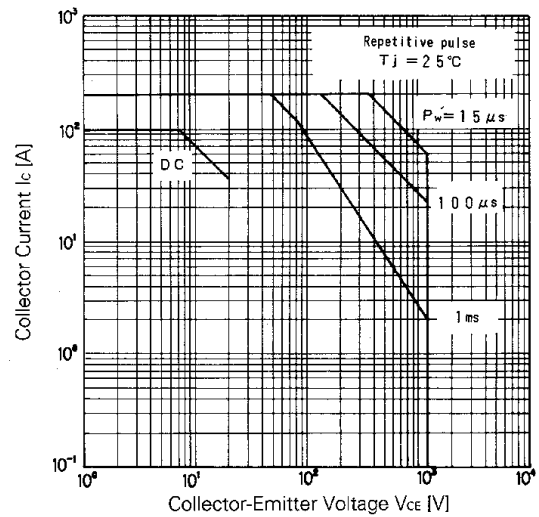
Dynamic Input Characteristic



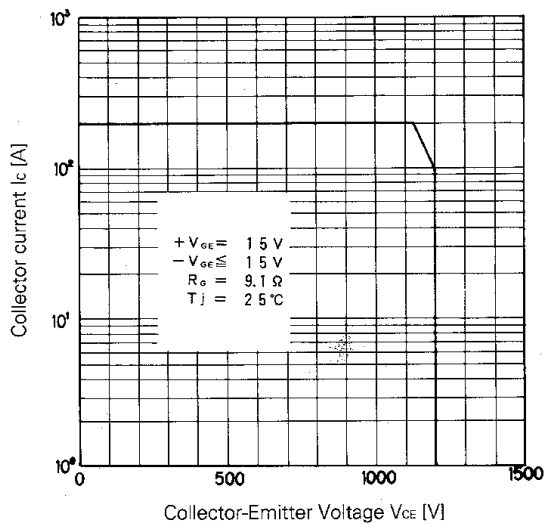
Forward Voltage of Free Wheel Diode



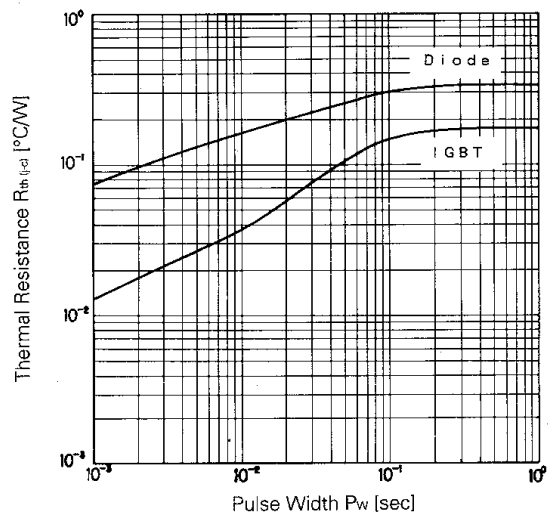
T_{rr} , I_{rr} - I_f



Safe Operating Area



Reverse Biased Safe Operating Area



Transient Thermal Resistance

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